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Substitute for form 1449A/B/PTO				Complete if Known	
				Application Number	10/663,741
				Filing Date	September 17, 2003
				First Named Inventor	Terry L. Gilton
				Art Unit	2811
				Examiner Name	Not Yet Assigned
Sheet	1	of	1	Attorney Docket Number	M4065.0656/P656

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U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)	MM-DD-YYYY		
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		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)	MM-DD-YYYY		

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NON PATENT LITERATURE DOCUMENTS					
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**INFORMATION DISCLOSURE
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Sheet **1** of **11** Attorney Docket Number **M4065.0656/P656**

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Examiner Initials*	Cite No. ¹	Document Number	Publication Date	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
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INFORMATION DISCLOSURE
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	Application Number	10/663,741			
	Filing Date	September 17, 2003			
	First Named Inventor	Terry L. Gilton			
	Art Unit	N/A			
	Examiner Name	Not Yet Assigned			
Sheet	2	of	11	Attorney Docket Number	M4065.0656/P656

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<input checked="" type="checkbox"/> AD4	2003/0209971	11/13/2003	Kozicki et al		
<input checked="" type="checkbox"/> AE4	2003/0210564	11/13/2003	Kozicki et al		
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<input checked="" type="checkbox"/> BB	WO 97/48032		12/18/1997	Kozicki et al.		
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Examiner Signature

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Sheet	4	of	11	First Named Inventor	Terry L. Gilton
				Group Art Unit	N/A
				Examiner Name	Not Yet Assigned
				Attorney Docket Number	M4065.0656/P656

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS					
Examiner Initials	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.			T ²
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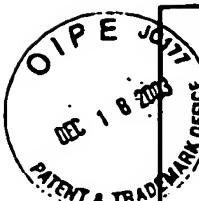
INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Substitute for form 1448B/PTO			Complete If Known		
			Application Number	10/663,741	
			Filing Date	September 17, 2003	
			First Named Inventor	Terry L. Gilton	
			Group Art Unit	N/A	
			Examiner Name	Not Yet Assigned	
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First Named Inventor	Terry L. Gilton
Group Art Unit	N/A
Examiner Name	Not Yet Assigned

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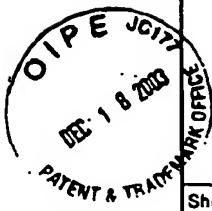
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Examiner Signature	<i>J. Gilton</i>	Date Considered	12-12-04
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Substitute for form 1449A/B/PTO				Complete If Known	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT				Application Number	10/663,741-Conf. #2658
(Use as many sheets as necessary)				Filing Date	September 17, 2003
Sheet	1	of	1	First Named Inventor	Terry L. Gilton
				Art Unit	2811
				Examiner Name	Not Yet Assigned
				Attorney Docket Number	M4065.0656/P656

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number Number-Kind Code ² (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear

FOREIGN PATENT DOCUMENTS					
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<i>On</i>	CA	YOJI KAWAMOTO et al., "Ionic Conduction In As ₂ S ₃ -Ag ₂ S, GeS ₂ -GeS ₂ -GeS-Ag ₂ S and P ₂ S ₅ -Ag ₂ S Glasses," Journal of Non-Crystalline Solids 20 (1976) 393-404.			

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CR	A	US 2004/0035401	2/2004	Ramachandran et al.	
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				Examiner Name	Not Yet Assigned
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Sheet	3	of	3		Attorney Docket Number	M4065.0656/P656

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